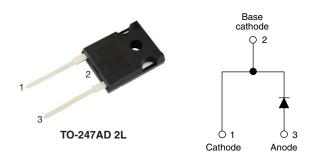
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Hyperfast Rectifier, 30 A FRED Pt[®]



PRIMARY CHARACTERISTICS								
I _{F(AV)}	30 A							
V _R	600 V							
V _F at I _F	1.34 V							
t _{rr} typ.	See Recovery table							
T _J max.	175 °C							
Package	TO-247AD 2L							
Circuit configuration	Single							

FEATURES

- · Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Single diode device
- Designed and qualified according to JEDEC[®]-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Peak repetitive reverse voltage	V _{RRM}		600	V					
Average rectified forward current	I _{F(AV)}	T _C = 116 °C	30	А					
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	300	~					
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS					
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-				
Forward voltage	V _F	I _F = 30 A	-	2.0	2.6	V			
		I _F = 30 A, T _J = 150 °C	-	1.34	1.75				
		V _R = V _R rated	-	0.3	50				
Reverse leakage current	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	60	500	μA			
Junction capacitance	CT	V _R = 600 V	-	33	-	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	3.5	-	nH			

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RoHS COMPLIANT HALOGEN FREE



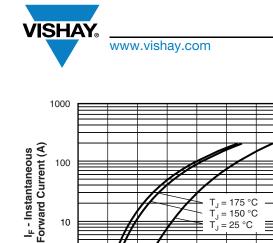
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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$			35				
Reverse recovery time	t _{rr}	$T_J = 25 \ ^\circ C$		-	31	-	ns			
		T _J = 125 °C		-	77	-				
Deals receivers aurrent	I _{RRM}	T _J = 25 °C	I _F = 30 A dI _F /dt = 200 A/μs V _B = 200 V	-	3.5	-	A			
Peak recovery current		T _J = 125 °C		-	7.7	-	A			
Deverage we can use a barrage	0	T _J = 25 °C		-	65	-	nC			
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	345	-	nc			

THERMAL - MECHANIC	THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS					
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C					
Thermal resistance, junction to case per leg	R _{thJC}		-	0.5	0.9						
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W					
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.4	-						
Weight			-	6.0	-	g					
Weight			-	0.22	-	oz.					
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)					
Marking device		Case style TO-247AD 2L		30EP	H06L						





10

1

0

0.5

1

1.5

V_F - Forward Voltage Drop (V)

Fig. 1 - Typical Forward Voltage Drop Characteristics

2

 $T_J = 150$ $T_J = 25 °C$ = 150 °C

2.5

3

3.5

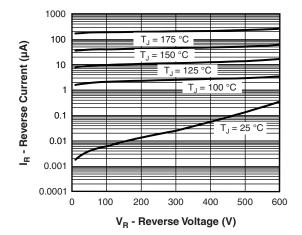


Fig. 2 - Typical Values of Reverse Current vs. **Reverse Voltage**

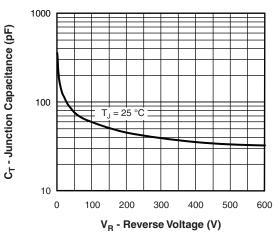
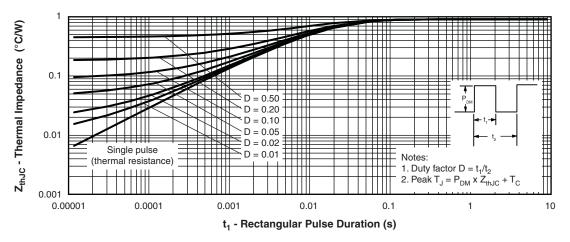
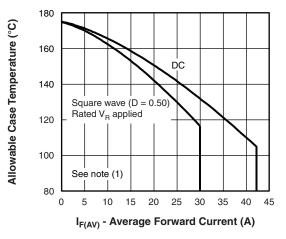


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage









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Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

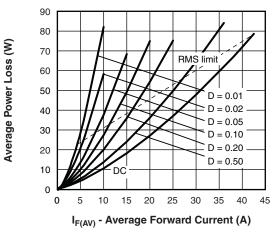


Fig. 6 - Forward Power Loss Characteristics

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}/D$) (see fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

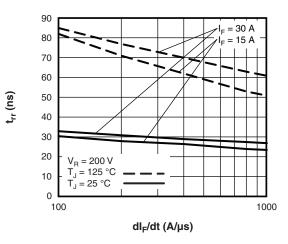


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

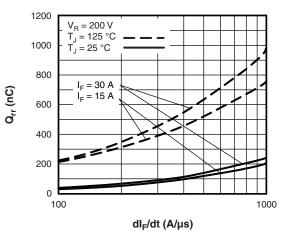
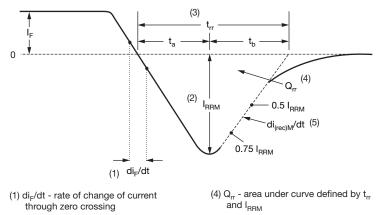


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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VS-30EPH06L-N3

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- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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Device code	VS-	30	Е	Р	н	06	L	-N3
		(2)	(3)	(4)	(5)	(6)	(7)	(8)
			<u> </u>				0	Ú
	<u> </u> 1		•	niconduo		oduct		
	2 -			ng (30 =				
	3 -	Circ	cuit conf	iguratio	า:			
		E =	single	diode				
	4 -	Pac	kage:					
		P =	TO-247	7				
	5	н =	hyperfa	ast recov	very			
	6 -	Vol	age rati	ing (06 =	= 600 V))		
	7 -	L =	long lea	ad				
	8 -	Env	ironmer	ntal digit	:			
		-N3	= halog	jen-free,	RoHS-	complia	ant, and	totally le

ORDERING INFO	RMATION (Example)		
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-30EPH06L-N3	25	500	Antistatic plastic tube

LINKS TO RELATED DOCUMENTS						
www.vishay.com/doc?95536						
www.vishay.com/doc?95648						
www.vishay.com/doc?96573						

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TO-247AD 2L

DIMENSIONS in millimeters and inches



Section C - C, D - D

(b, b2)

(4)

View	<u>/ B</u>

SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STMDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209			E	15.29	15.87	0.602	0.625	3
A1	2.21	2.59	0.087	0.102			E1	13.46	-	0.53	-	
A2	1.50	2.49	0.059	0.098			е	5.46	BSC	0.215	5 BSC	
b	0.99	1.40	0.039	0.055			ØК	0.2	254	0.0	010	
b1	0.99	1.35	0.039	0.053			L	19.81	20.32	0.780	0.800	
b2	1.65	2.39	0.065	0.094			L1	3.71	4.29	0.146	0.169	
b3	1.65	2.34	0.065	0.092			ØР	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035			Ø P1	-	6.98	-	0.275	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	' BSC	
D2	0.51	1.35	0.020	0.053				•		•		•

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

(5) Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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